

BAV99W, BAV99RW

SC-70/SOT-323 Dual Series Switching Diodes

The BAV99WT1G is a smaller package, equivalent to the BAV99LT1G.

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

Suggested Applications

- ESD Protection
- Polarity Reversal Protection
- Data Line Protection
- Inductive Load Protection
- Steering Logic

MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	100	Vdc
Forward Current	I_F	215	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current (Note 1) (averaged over any 20 ms period)	$I_{F(AV)}$	715	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-Repetitive Peak Forward Current t = 1.0 μ s t = 1.0 ms t = 1.0 s	I_{FSM}	2.0 1.0 0.5	A

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 × 0.75 × 0.062 in.

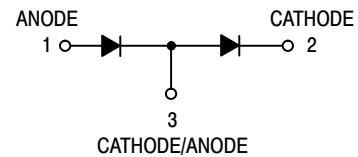


ON Semiconductor®

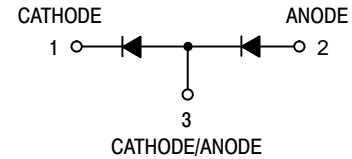
www.onsemi.com



SC-70
CASE 419

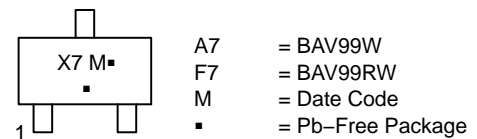


BAV99WT1
SC-70, CASE 419, STYLE 9



BAV99RWT1
SC-70, CASE 419, STYLE 10

MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping†
BAV99WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SBAV99WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
BAV99RWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SBAV99RWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
NSVBAV99WT3G	SC-70 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BAV99W, BAV99RW

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	200 1.6	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Each Diode)

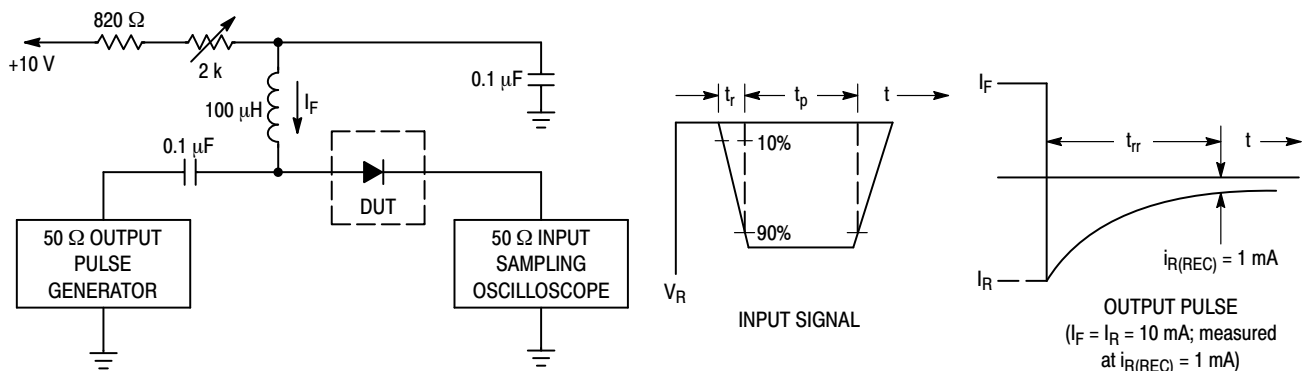
Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Reverse Breakdown Voltage ($I_{(BR)} = 100 \mu\text{A}$)	$V_{(BR)}$	100	-	Vdc
Reverse Voltage Leakage Current ($V_R = 100 \text{Vdc}$) ($V_R = 25 \text{Vdc}, T_J = 150^\circ\text{C}$) ($V_R = 70 \text{Vdc}, T_J = 150^\circ\text{C}$)	I_R	- - -	1.0 30 50	μA dc
Diode Capacitance ($V_R = 0, f = 1.0 \text{MHz}$)	C_D	-	1.5	pF
Forward Voltage ($I_F = 1.0 \text{mA}$) ($I_F = 10 \text{mA}$) ($I_F = 50 \text{mA}$) ($I_F = 150 \text{mA}$)	V_F	- - - -	715 855 1000 1250	mVdc
Reverse Recovery Time ($I_F = I_R = 10 \text{mA}$, $i_{R(REC)} = 1.0 \text{mA}$) (Figure 1) $R_L = 100 \Omega$	t_{rr}	-	6.0	ns
Forward Recovery Voltage ($I_F = 10 \text{mA}, t_r = 20 \text{ns}$)	V_{FR}	-	1.75	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



- Notes: (a) A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA.
 (b) Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10 mA.
 (c) $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

BAV99W, BAV99RW

CURVES APPLICABLE TO EACH DIODE

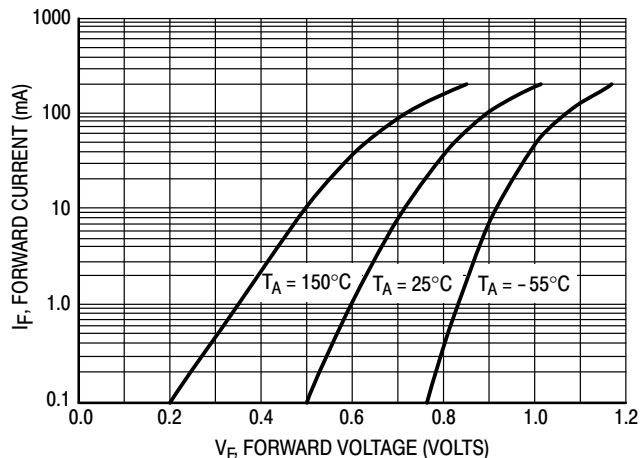


Figure 2. Forward Voltage

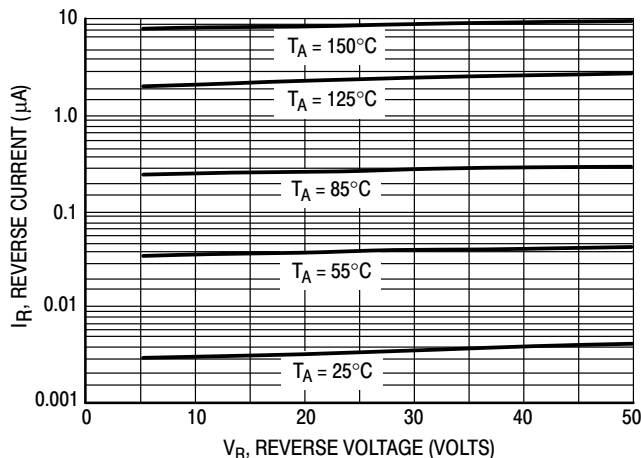


Figure 3. Leakage Current

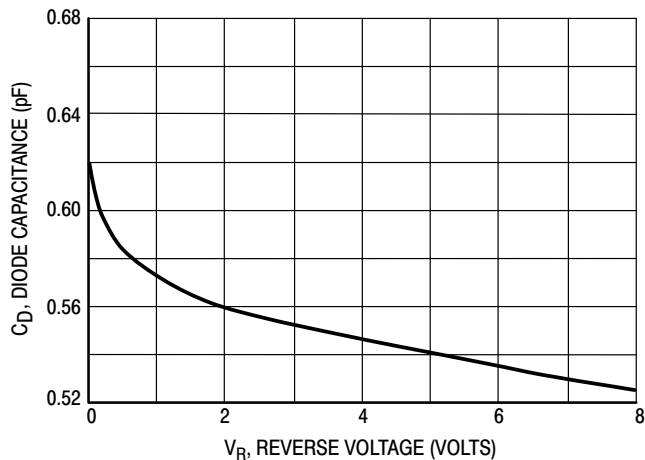
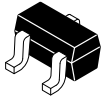


Figure 4. Capacitance

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

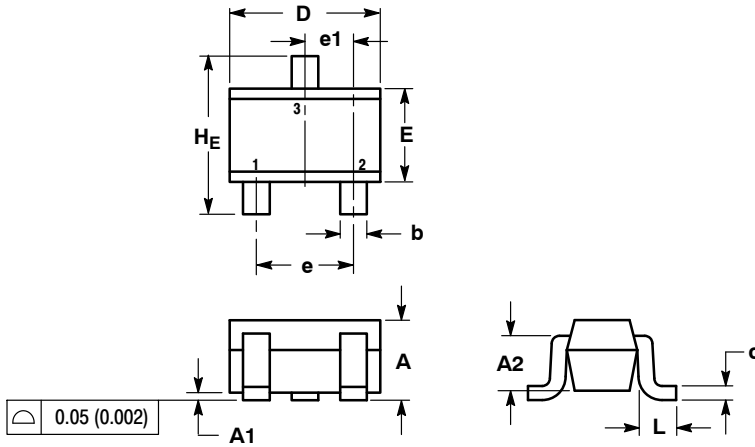
ON Semiconductor®



SCALE 4:1

SC-70 (SOT-323)
CASE 419-04
ISSUE N

DATE 11 NOV 2008

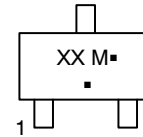


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

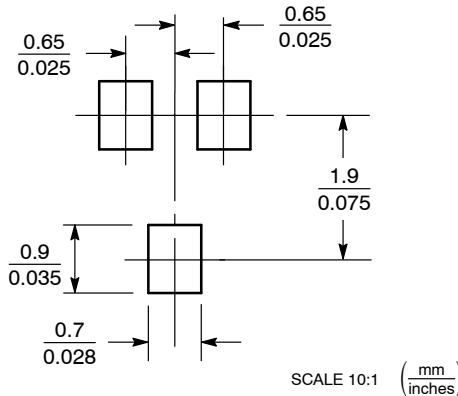
GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- | | | | | | |
|---|---|---|--|---|---|
| STYLE 1:
CANCELLED | STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE | STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE | |
| STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR | STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN | STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE | STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE-CATHODE | STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE |

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:
Voice Mail: 1 800-282-9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative